

TOSHIBA Diode Silicon Epitaxial Schottky Barrier Type

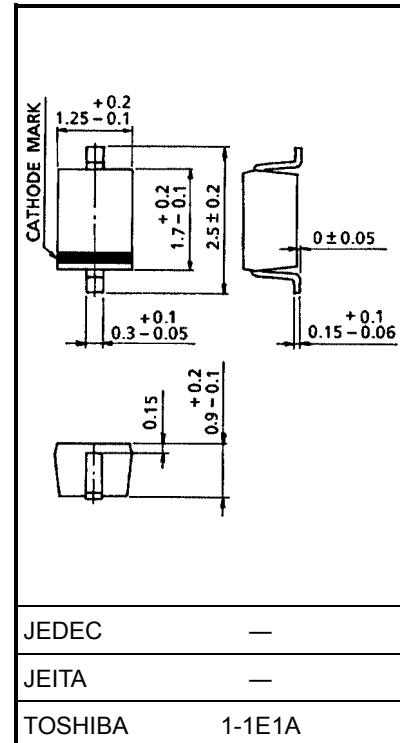
1SS315

UHF Band Mixer Applications

Unit: mm

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V _{RM}	5	V
Forward current	I _F	30	mA
Junction temperature	T _j	125	°C
Storage temperature range	T _{stg}	-55~125	°C



Weight: 0.004 g (typ.)

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Forward voltage	V _F	I _F = 2 mA	—	0.25	—	V
Forward current	I _F	V _F = 0.5 V	30	—	—	mA
Reverse current	I _R	V _R = 0.5 V	—	—	25	μA
Total capacitance	C _T	V _R = 0.2 V, f = 1 MHz	—	0.6	—	pF

Marking